

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|---|---|------------------|---------|------------------|
| L1 | 2810 | 257/347.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/28 07:18 |
| L2 | 0 | adhesive with semiconductor with continuous with porous with layer | US-PGPUB | OR | ON | 2005/11/28 07:19 |
| S1 | 2 | "6774010" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/14 15:39 |
| S2 | 11 | (adhesive with semiconductor with porous) and nm | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/18 14:41 |
| S3 | 1 | ((adhesive with semiconductor with porous) and nm) and MOS | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/18 14:42 |
| S4 | 11 | (adhesive with semiconductor with porous) and nm | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/18 15:18 |
| S5 | 1 | "6100166" and (high with resistance) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/18 15:20 |
| S6 | 15 | "6100166" and (nitride or high-k) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/18 15:20 |
| S7 | 103 | adhesive with semiconductor with porous | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/19 12:34 |
| S8 | 236922 | (adhesive with semiconductor with porous) and FET or MOS or bipolar | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/19 12:34 |

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| S9 | 3 | (adhesive with semiconductor with porous) and (FET or MOS or bipolar) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/19 12:35 |
| S10 | 4 | (US-20020000242-\$ or US-20030017712-\$).did. or (US-6100166-\$ or US-6350945-\$). did. | US-PGPUB; USPAT | OR | ON | 2005/02/14 17:34 |
| S13 | 2 | S10 and monocrystalline | US-PGPUB; USPAT | OR | ON | 2005/02/14 17:36 |
| S14 | 4 | S10 and adhesive | US-PGPUB; USPAT | OR | ON | 2005/02/14 17:37 |
| S15 | 4 | S10 and (adhesive with substrate) | US-PGPUB; USPAT | OR | ON | 2005/02/14 17:38 |
| S16 | 0 | S10 and MOS | US-PGPUB; USPAT | OR | ON | 2005/02/14 17:38 |
| S17 | 2 | S10 and transistor | US-PGPUB; USPAT | OR | ON | 2005/02/14 17:38 |
| S18 | 4 | (US-20020000242-\$ or US-20030017712-\$).did. or (US-6100166-\$ or US-6350945-\$). did. | US-PGPUB; USPAT | OR | ON | 2005/06/07 11:04 |
| S19 | 4 | S18 and porous | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 11:07 |
| S20 | 4 | S19 and adhesive | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 11:07 |
| S21 | 4 | S20 and substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 11:08 |
| S22 | 0 | S21 and CMOS | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 11:08 |
| S23 | 0 | S21 and MOS | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 11:08 |

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| S24 | 1 | S21 and FET | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 11:08 |
| S25 | 4 | (US-20020000242-\$ or US-20030017712-\$).did. or (US-6100166-\$ or US-6350945-\$). did. | US-PGPUB; USPAT | OR | ON | 2005/06/07 12:44 |
| S26 | 4 | S25 and porous | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 12:44 |
| S27 | 4 | S26 and adhesive | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 12:44 |
| S28 | 4 | S27 and substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/07 12:44 |